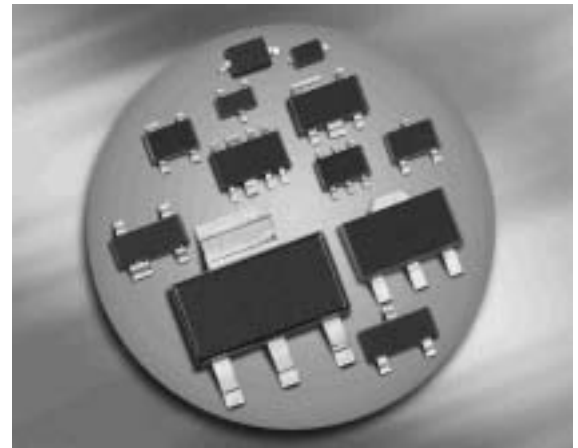
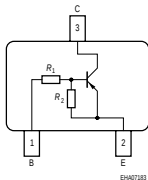


PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1 = 47k\Omega$, $R_2 = 22k\Omega$)
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101



BCR196/F BCR196W



Type	Marking	Pin Configuration						Package
BCR196	WXs	1=B	2=E	3=C	-	-	-	SOT23
BCR196F	WXs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR196W	WXs	1=B	2=E	3=C	-	-	-	SOT323

¹Pb-containing package may be available upon special request

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	80	
Input reverse voltage	$V_{i(rev)}$	10	
Collector current	I_C	70	mA
Total power dissipation-	P_{tot}		mW
BCR196, $T_S \leq 102^\circ\text{C}$		200	
BCR196F, $T_S \leq 128^\circ\text{C}$		250	
BCR196W, $T_S \leq 124^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	150 ... -65	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR196		≤ 240	
BCR196F		≤ 90	
BCR196W		≤ 105	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}$, $I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$, $I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}$, $I_C = 0$	I_{EBO}	-	-	220	μA
DC current gain ²⁾ $I_C = 5 \text{ mA}$, $V_{CE} = 5 \text{ V}$	h_{FE}	50	-	-	-
Collector-emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}$, $I_B = 0,5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}$, $V_{CE} = 5 \text{ V}$	$V_{i(off)}$	1.2	-	2.6	
Input on voltage $I_C = 2 \text{ mA}$, $V_{CE} = 0,3 \text{ V}$	$V_{i(on)}$	1.5	-	4	
Input resistor	R_1	32	47	62	k Ω
Resistor ratio	R_1/R_2	1.92	2.14	2.36	-

AC Characteristics

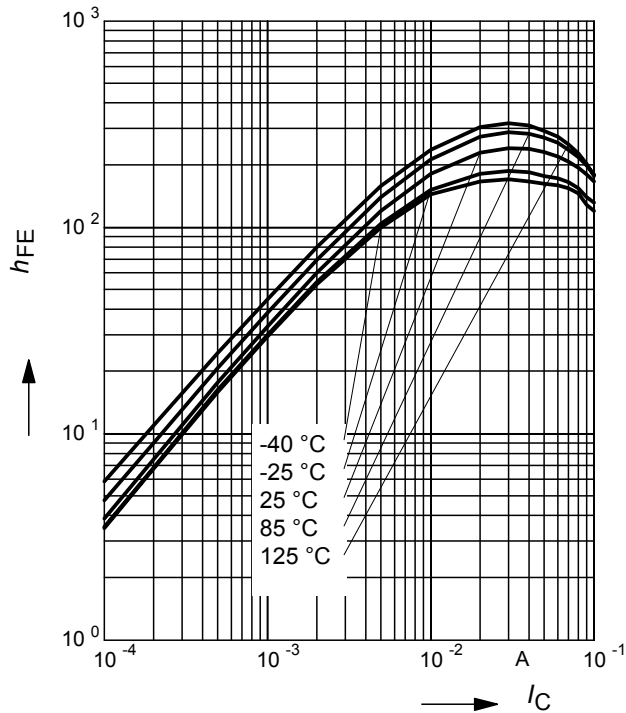
Transition frequency $I_C = 10 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $f = 100 \text{ MHz}$	f_T	-	150	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

²⁾Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$

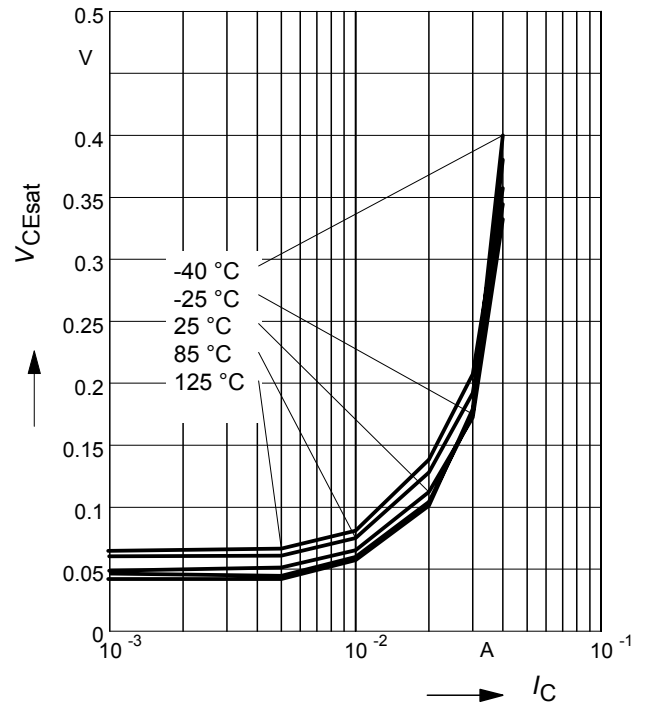
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



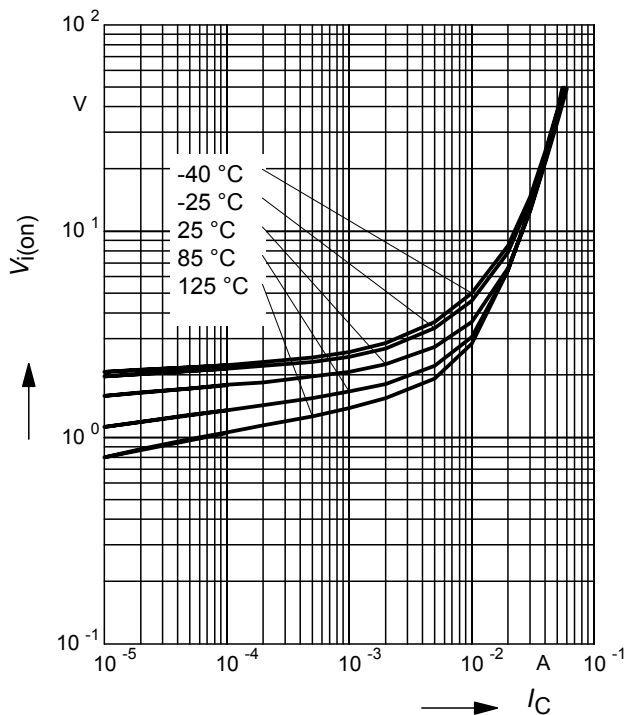
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C)$, $I_C/I_B = 20$



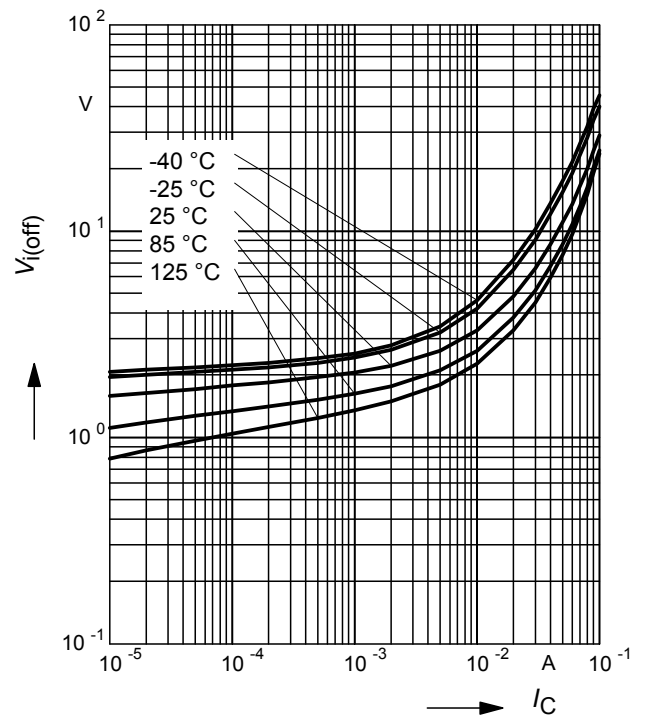
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3 \text{ V}$ (common emitter configuration)



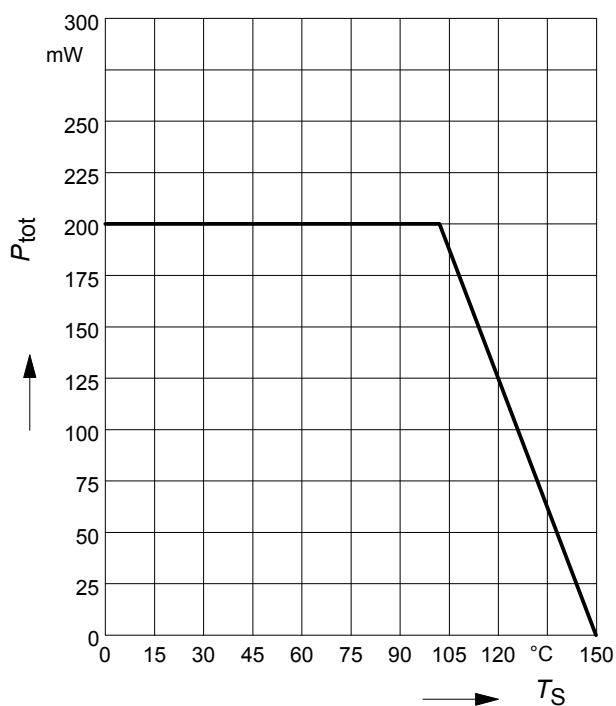
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



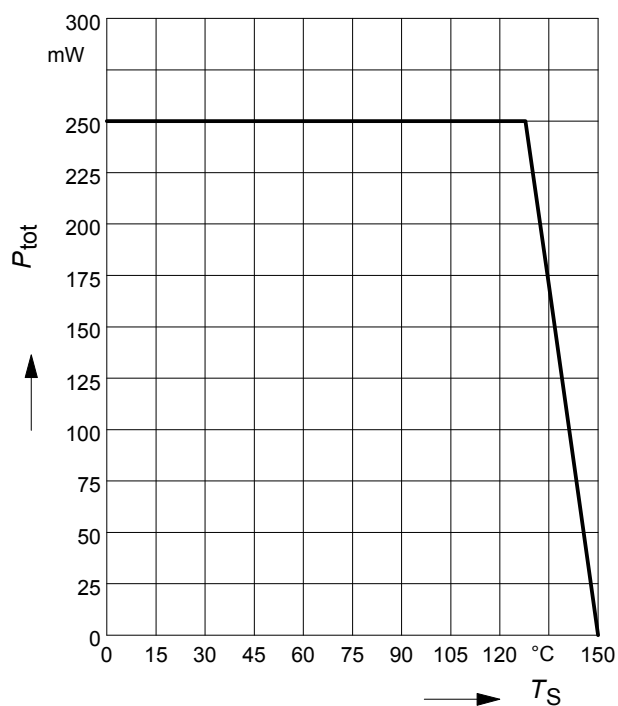
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR196



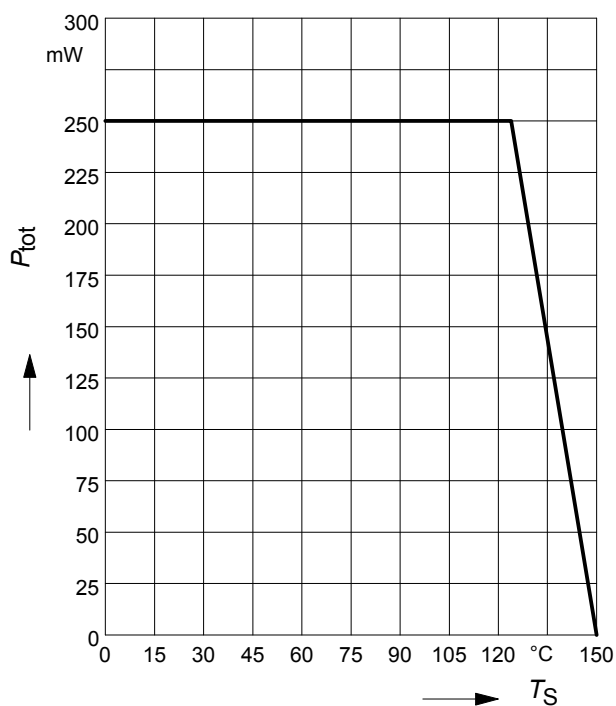
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR196F



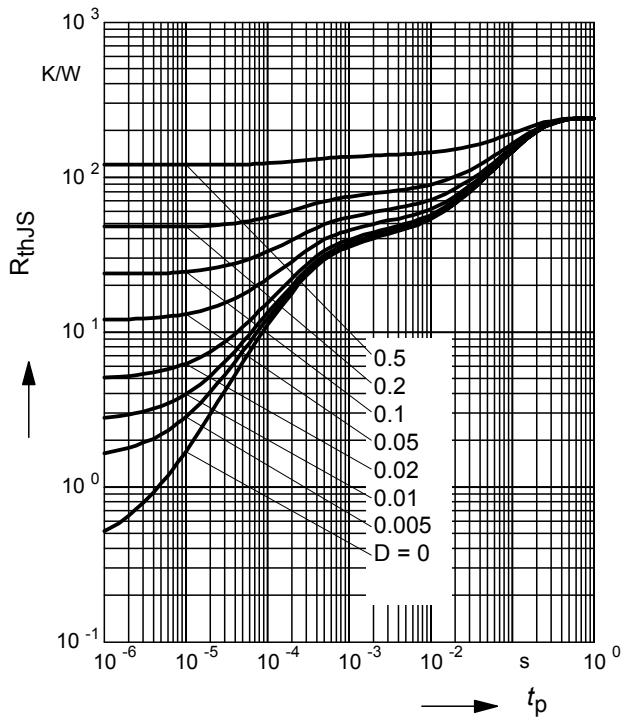
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR196W



Permissible Pulse Load $R_{thJS} = f(t_p)$

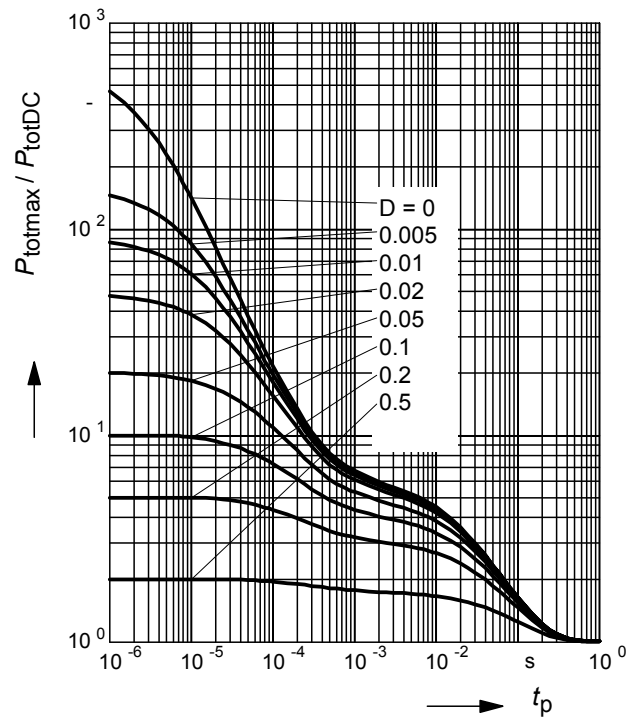
BCR196



Permissible Pulse Load

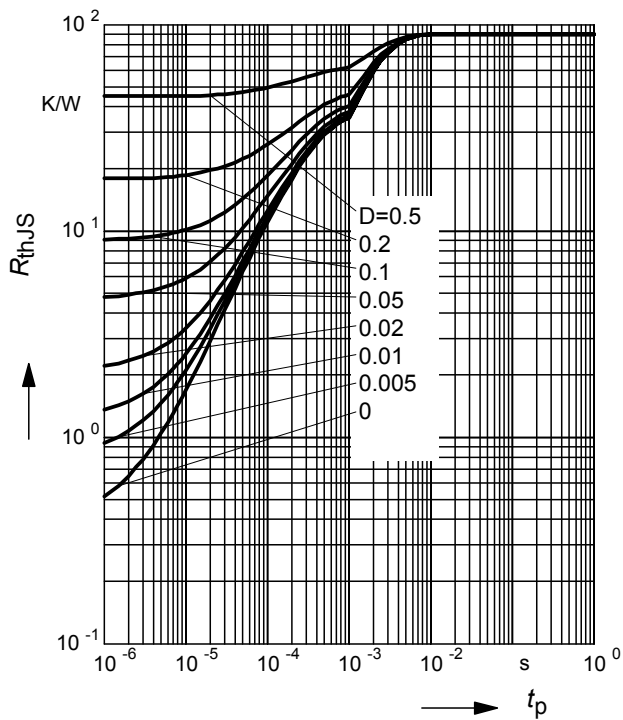
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR196



Permissible Puls Load $R_{thJS} = f(t_p)$

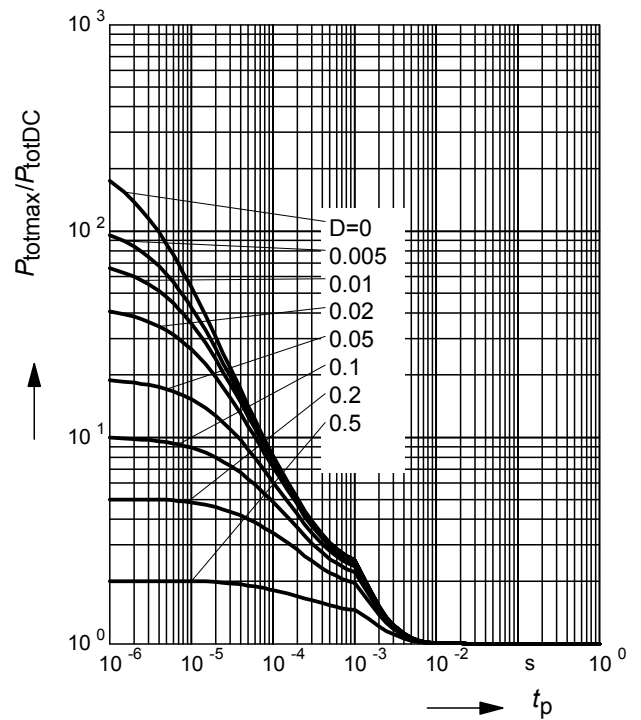
BCR196F



Permissible Pulse Load

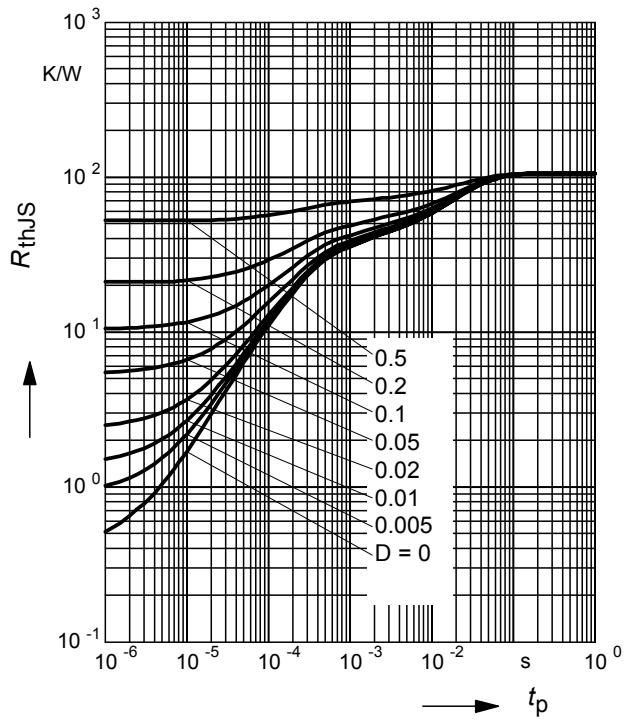
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR196F



Permissible Puls Load $R_{thJS} = f(t_p)$

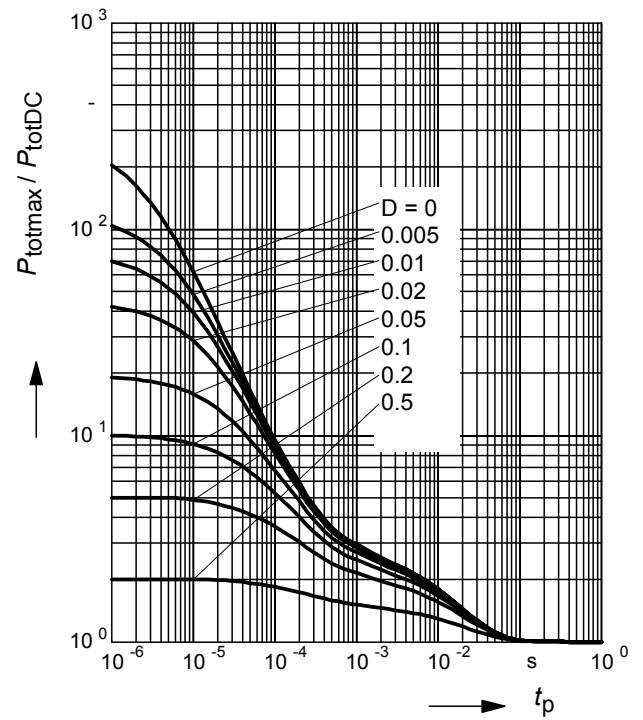
BCR196W

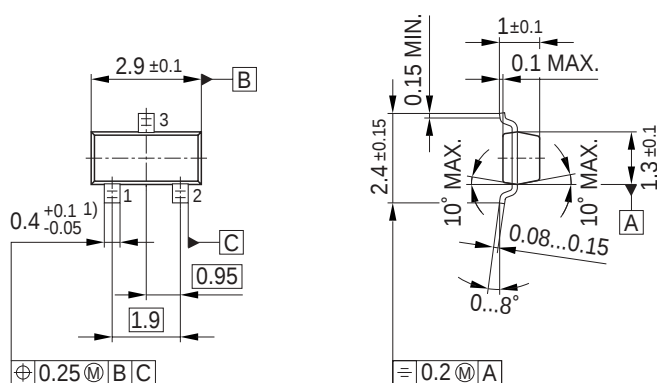


Permissible Pulse Load

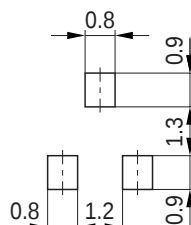
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR196W





Foot Print



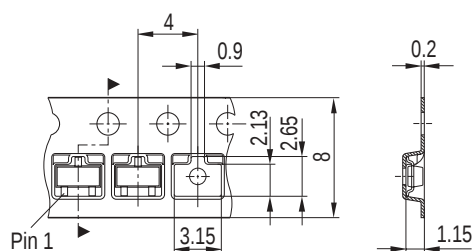
Infineon
Manufacturer

05 05
2005, June
Date code (YM)

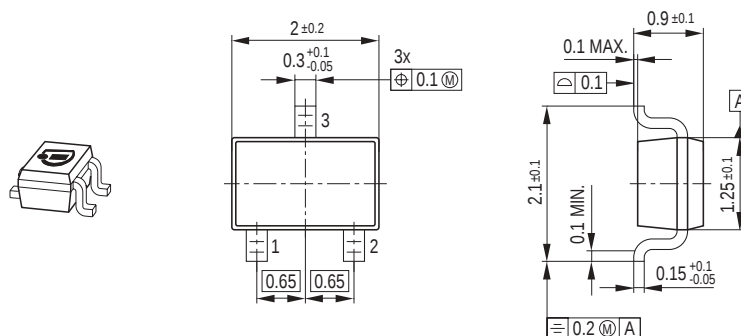
Pin 1

BCW66
Type code

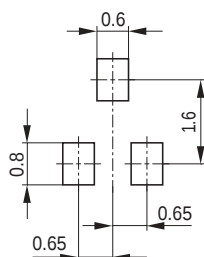
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



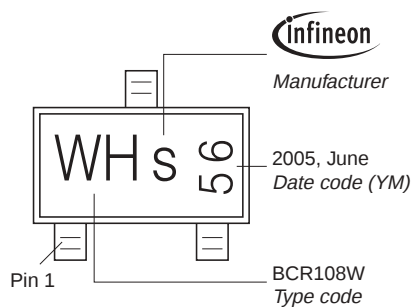
Package Outline



Foot Print

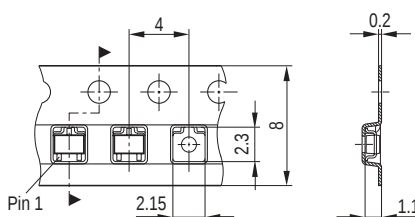


Marking Layout (Example)



Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel



The technical drawing shows two views of the M8x10mm connector:

- Front View (Left):** Shows the top profile of the connector. Dimensions include a total width of 1.2 ± 0.05 , a central slot width of 0.2 ± 0.05 , a pin diameter of $\varnothing 3$, and mounting hole positions at 0.2 ± 0.05 , 0.4 ± 0.05 , and 0.4 ± 0.05 from the edges.
- Side View (Right):** Shows the side profile of the connector. Dimensions include a total height of 1.2 ± 0.05 , a base thickness of 0.2 ± 0.05 , a top flange width of 0.55 ± 0.04 , a bottom flange width of 0.15 ± 0.05 , and a maximum taper angle of 10° MAX. . The overall depth is 0.8 ± 0.05 .

Technical drawing of a mechanical part with dimensions: 0.4, 0.45, 1.05, and 0.4.

Diagram illustrating the marking on the BCR847BF diode:

- infineon**: Manufacturer
- 1F S**: Type code
- Pin 1**: Cathode

Technical drawing of a mechanical part showing a top view and a side view. The top view includes dimensions: 4, 0.3, 1.2, 1.5, 8, 1.35, and Pin 1. The side view includes dimensions: 0.2 and 0.7.

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